



DECLARATION FOR PATENT APPLICATION

(03S0338)

As a below named inventor, I declare that my residence, mailing address and citizenship are as stated below above my name; I believe that I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled:

SEMICONDUCTOR DEVICE HAVING VERTICAL MOS GATE STRUCTURE AND METHOD OF MANUFACTURING THE SAME

the specification of which (check applicable box(es))

☐ is attached hereto.

☒ was filed on April 22, 2004 as United States Application No. 10/829,173

or PCT International Application No.

☐ and was amended on

I hereby state that I have reviewed and understand the contents of the aboveidentified specification, including the claims, as amended by any amendment referred to above.

I acknowledge the duty to disclose information which is material to patentability as defined in 37 CFR 1.56.

I hereby claim foreign priority benefits under 35 U.S.C. 119(a)-(d) or 365(b) of any foreign application(s) for patent or inventor's certificate, or 35 U.S.C. 365(a) of any PCT International application which designated at least one country other than the United States, listed below and have also identified below any foreign application for patent or inventor's certificate, or PCT International application having a filing date before that of the application on which priority is claimed:

Country	Category	Application Number	Filing Date	Priority Claim
Japan	Patent	2003-118462	April 23, 2003	Yes

I hereby appoint as my attorneys, with full power of substitution and revocation, to prosecute this application and transact all business in the Patent and Trademark Office connected therewith: the practitioners at:

Customer Number : 22850

of Oblon, Spivak, McClelland, Maier & Neustadt, P.C.. Please address all correspondence and telephone communications to the address and telephone number for this Customer Number.

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.



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(03S0338)

I declare further that my citizenship, residence and mailing address are as stated below next to my name:

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Syotaro Ono

Syotaro Ono

MAY. 28. 2004

Date:

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Yusuke Kawaguchi

Yusuke Kawaguchi

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Date:

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Akio Nakagawa

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MAY. 28. 2004

Date: